Multilayer Chip Power Inductor – MPH Series

Operating Temp. : -40 ℃~+85 ℃



FEATURES

- High DC bias current due to trench technology
- Low profile and thin thickness
- Monolithic structure for high reliability
- Excellent solderability and high heat resistance
- No cross coupling due to magnetic shield

APPLICATIONS

DC-DC converter circuits for mobile phones, DSCs, DVCs, HDDs, PDAs, etc.

PRODUCT IDENTIFICATION

<u>MPH</u>	<u>201210</u>	<u>s</u>	<u>4R7</u>	<u>M</u>	<u> </u>	•	
1	2	3	4	5	6		
1		2			3		
	Туре	Externa	al Dimension	s (L×W×H) (mm)		F	eature Type
MPH	Chip Power Inductor	201	1210	2.0×1.25×1.0	;	S	Standard
	<u> </u>	201	1610	2.0×1.6×1.0	<u>-</u>		
4		252	2010	2.5×2.0×1.0			

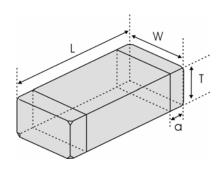
Nominal Inductance						
Example Nominal Value						
R47	0.47µH					
4R7	4.7uH					

5							
Inductance Tolerance							
M	±20%						
N	±30%						

6	
	Packing
Т	Tape & Reel

SHAPE AND DIMENSIONS

Unit: mm [inch]



Type	L	W	T	а	
201210	2.0 (+0.3, -0.1)	1.25±0.2	0.9±0.1	0.5±0.3	
	[.079 (+.012,004)]	[.049±.008]	[.035±.004]	[.020±.012]	
201610	2.0 (+0.3, -0.1)	1.6±0.2	0.9±0.1	0.5±0.3	
	[.079 (+.012,004)]	[.063±.008]	[.035±.004]	[.020±.012]	
252010	2.5±0.2	2.0 (+0.3, -0.1)	0.9±0.1	0.5±0.3	
	[.098±.008]	[.079 (+.012,004)]	[.035±.004]	[.020±.012]	

SPECIFICATIONS

MPH201210 TYPE

Part Number	Inductance	L Test Freq.	Min. Self-resonant Frequency	DC Resistance	Temperature Rise Current Max.	Saturation Current Typ.	Thickness
Units	μH	MHz	MHz	Ω	mA	mA	mm [inch]
Symbol	L	Freq.	S.R.F	DCR	Irms*	Isat*	Т
MPH201210SR47□T	0.47	1	100	0.08±25%	1500	1200	
MPH201210S1R0□T	1.0	1	60	0.11±25%	1300	1150	
MPH201210S1R5□T	1.5	1	50	0.16±25%	1100	800	0.9±0.1
MPH201210S2R2□T	2.2	1	40	0.20±25%	900	500	[.035±.004]
MPH201210S3R3□T	3.3	1	30	0.20±25%	900	350	
MPH201210S4R7□T	4.7	1	30	0.25±25%	800	280	

MPH201610 TYPE

Part Number	Inductance	L Test Freq.	Min. Self-resonant Frequency	DC Resistance	Temperature Rise Current Max.	Saturation Current Typ.	Thickness
Units	μH	MHz	MHz	Ω	mA	mA	mm [inch]
Symbol	L	Freq.	S.R.F	DCR	Irms*	lsat*	Т
MPH201610SR47□T	0.47	1	100	0.08±25%	1500	1600	
MPH201610S1R0□T	1.0	1	70	0.09±25%	1400	1200	
MPH201610S1R5□T	1.5	1	60	0.11±25%	1200	700	0.9±0.1
MPH201610S2R2□T	2.2	1	50	0.11±25%	1200	500	[.035±.004]
MPH201610S3R3□T	3.3	1	40	0.12±25%	1200	330	
MPH201610S4R7□T	4.7	1	30	0.14±25%	1100	220	

MPH252010 TYPE

WII 11202010 111 E									
Part Number	Inductance	L Test Freq.	Min. Self-resonant Frequency	DC Resistance	Temperature Rise Current Max.	Saturation Current Typ.	Thickness		
Units	μH	MHz	MHz	Ω	mA	mA	mm [inch]		
Symbol	L	Freq.	S.R.F	DCR	Irms*	lsat*	Т		
MPH252010SR47□T	0.47	1	105	0.04±25%	1800	1500			
MPH252010S1R0□T	1.0	1	70	0.06±25%	1600	1400			
MPH252010S1R5□T	1.5	1	65	0.07±25%	1500	1200	0.9±0.1		
MPH252010S2R2□T	2.2	1	55	0.08±25%	1300	850	[.035±.004]		
MPH252010S3R3□T	3.3	1	30	0.10±25%	1200	450			
MPH252010S4R7□T	4.7	1	25	0.11±25%	1100	320			

^{※□:} Please specify the inductance tolerance code (M=±20%, N=±30%).

 $[\]rm \%Irms$: DC current causes temperature rise of 40 $^{\circ}\rm C$ from 20 $^{\circ}\rm C$ ambient.

XIsat: DC current at which the inductance drops approximate 30% from its value without current.